



65C00 MICROPROCESSORS

THE 65C00 MICROPROCESSOR FAMILY CONCEPT -

The 65C00 Series Microprocessors represent the first totally software compatible microprocessor family. This family of products includes a range of software compatible microprocessors which provide a selection of addressable memory range, interrupt input options and on-chip clock oscillators and drivers. All of the microprocessors in the 65C00 group are software compatible within the group and are bus compatible with the M6800 product offering.

The family includes six microprocessors with on-board clock oscillators and drivers and four microprocessors driven by external clocks. The on-chip clock versions are aimed at high performance, low cost applications where single phase inputs, crystal or RC inputs provide the time base. The external clock versions are geared for the multi processor system applications where maximum timing control is mandatory. All versions of the microprocessors are available in 1 MHz maximum operating frequencies.



- Single +5 volt supply
- · Eight bit parallel processing
- 56 Instructions
- Decimal and binary arithmetic
- Thirteen addressing modes
- True indexing capability
- Programmable stack pointer
- Variable length stack
- Interrupt capability
- Non-maskable interrupt
- Use with any type or speed memory
- 8 BIT Bi-directional Data Bus
- Addressable memory range of up to 65K bytes
- "Ready" input (for single cycle execution)
- Direct memory access capability
- Bus compatible with M6800
- Choice of external or on-board clocks
- 1 MHz operation
- On-the-chip clock options *External single clock input
 *RC time base input
 *Crystal time base input
- Pipeline architecture

MEMBERS OF THE 65C00 MICROPROCESSOR (CPU) FAMILY

Microprocessors with On-Chip Clock Oscillator

Model	Addressable Memory
MPS65C02	65K Bytes
MPS65C03	4K Bytes
MPS65C04	8K Bytes
MPS65C05	4K Bytes
MPS65C06	4K Bytes
MPS65C07	8K Bytes
Microprocessors Clock Inputs	with External Two Phase
MPS65C12	65K Bytes
MPS65C13	4K Bytes
MPS65C14	8K Bytes
MPS65C15	4K Bytes







COMMENTS ON THE DATA SHEET

The data sheet is constructed to review first the basic "Common Characteristics"—those features which are common to the general family of microprocessors. Subsequent to a review of the family characteristics will be sections devoted to each member of the group with specific features of each.





65C00

COMMON CHARACTERISTICS

MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
SUPPLY VOLTAGE	Vcc	- 0.3 to + 7.0	Vdc
INPUT VOLTAGE	Vin	-0.3 to +7.0	Vdc
OPERATING TEMPERATURE	TA	0 to +70	۰C
STORAGE TEMPERATURE	TSTG	- 55 to + 150	•c

This device contains input protection against damage due to high static voltages or electric fields; however, precautions should be taken to avoid application of voltages higher than the maximum rating.

ELECTRICAL CHARACTERISTICS (Vcc = 5.0V ± 5%, Vss = 0, T_A = 0° to + 70°C) \emptyset_1, \emptyset_2 (in) applies to 65C12, 13, 14, 15; \emptyset_0 (in) applies to 65C02, 03, 04, 05, 06 and 07

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input High Voltage					
Logic,⊘ _{° (in)}		Vss + 2.4	-	Vcc	Vdc
Ø.,Ø.(in)	∨ін	Vcc - 0.2	-	Vcc + 1.0V	Vdc
Input High Voltage					
RES, NMI, RDY, IRQ, Data, S.O.		Vss + 2.0	-	-	Vdc
Input Low Voltage					
Logic,⊘. (in)		Vss - 0.3	- 1	Vss + 0.4	Vdc
Ø,Ø(in)	VIL	Vss - 0.3	-	Vss + 0.2	Vdic
RES, NMI, RDY, IRQ, Data, S.O.		-	-	Vss + 0.8	Vdc
Input Leakage Current					
(V _{in} = 0 to 5.25V, Vcc = 5.25V)					
Logic (Excl. RDY,S.O.)	lin	-	-	2.5	Αμ
Ø, Ø _(in)		-		100	۸ س
Ø _{°(In)}		-	-	10.0	Aµ
Three State (Off State) Input Current					
$(V_{in} = 0.4 \text{ to } 2.4V, Vcc = 5.25V)$					
Data Lines	ITSI	-	-	10	μA
Output High Voltage					
(I _{OH} = - 100µAdc, Vcc = 4.75V)	ł		ļ		
SYNC, Data, AO-A15, RW	VOH	Vss + 2.4	-	_	Vdc
Out Low Voltage					
(I _{OL} = 1.6mAdc, Vcc = 4.75V)					
SYNC, Data, AO-A15, RW	VOL	_	-	Vss + 0.4	Vdc
Supply Current	Icc	-		20	mA
Capacitance	с				pF
$(V_{in} = 0, T_A = 25^{\circ}C, f = 1MHz)$					
Logic	Cin		-	10	
Data]	-	_	15	
AO-A15,RW, SYNC	Cout	-	-	12	
Ø _{°(In)}	C _{ذ(in)}	-	-	15	
a	c _{ø,}	-	30	50	
Ø,	c _{∅,}		50	80	
	• • • • • • • • • • • • • •				

Note: IRQ and NMI require 3K pull-up resistors.





COMMON CHARACTERISTICS

1 MHz TIMING

Electrical Characteristics: (Vcc = 5V \pm 5%, Vss = 0 V, T_A = 0°-70°C)

CLOCK TIMING - 65C02, 03, 04, 05

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.
Cycle Time	Тсүс	1000	_	-
Ø _{O(IN)} Pulse Width (measured at 1.5v)	PWHØO	460	—	520
Ø _{0 (IN)} Rise, Fall Time	TRØ ₀ ,TFØ ₀	_	—	10
Delay Time between Clocks (measured at 1.5v)	т _D	5	—	-
Ø1(OUT) Pulse Width (measured at 1.5v)	PWHØ1	PWHØOL-20	-	PWHØOL
$Q_{2(OUT)}$ Pulse Width (measured at 1.5v)	PWHØ2	PWHØOH-40		PWHØOH-10
Ø1(OUT), Ø2(OUT) Rise, Fall Time (measured .8v to 2.0v) (Load ½ 30pf ½ 1 TTL)	T _R , T _F	-	_	25

CLOCK TIMING: 65C12, 13, 14, 15

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.
Cycle Time	Тсүс	1000	-	_
Clock Pulse Width Ø1 (Measured at V _{CC} — 0.2v) Ø2	PWH Ø1 PWH Ø2	430 470	_	_
Fall Time, Rise Time (Measured from 0.2v to V _{CC} — 0.2v)	T _F , T _R	—		25
Delay Time between Clocks (Measured at 0.2v)	Тр	0	—	_

READ/ WRITE TIMING (LOAD = ITTL)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.
Read/ Write Setup Time from 65C00	TRWS	_	100	300
Address Setup Time from 65C00	TADS	-	100	300
Memory Read Access Time	TACC	—	_	575
Data Stability Time Period	TDSU	100	_	-
Data Hold Time — Read	THR	10	—	-
Data Hold Time — Write	тнw	30	60	—
Data Setup Time from 65C00	TMDS	_	150	200
S.O. Setup Time	TS.O.	100	-	-
SYNC Setup Time from 6500	TSYNC	—	-	350
Address Hold Time	ТНА	30	60	—
R/W Hold Time	THRW	30	60	-
RDY Setup Time	TRDY	100	—	-





COMMON CHARACTERISTICS

65C00 SIGNAL DESCRIPTION

Clocks (Ø1, Ø2)

The 65C1X requires a two phase non-overlapping clock that runs at the Vcc voltage level.

The 65C0X clocks are supplied with an internal clock generator. The frequency of these clocks is externally controlled.

Address Bus (A₀-A₁₅)

These outputs are TTL compatible, capable of driving one standard TTL load and 130 pf.

Data Bus (D₀-D₇)

Eight pins are used for the data bus. This is a bi-directional bus, transferring data to and from the device and peripherals. The outputs are tri-state buffers capable of driving one standard TTL load and 130pf.

Data Bus Enable (DBE)

This TTL compatible input allows external control of the tri-state data output buffers and will enable the microprocessor bus driver when in the high state. In normal operation DBE would be driven by the phase two (\mathcal{O}_2) clock, thus allowing data output from microprocessor only during \mathcal{O}_2 . During the read cycle, the data bus drivers are internally disabled, becoming essentially an open circuit. To disable data bus drivers externally, DBE should be held low.

Ready (RDY)

This input signal allows the user to single cycle the microprocessor on all cycles except write cycles. A negative transition to the low state during or coincident with phase one (\emptyset_1) and up to 100ns after phase two (\emptyset_2) will halt the microprocessor with the output address lines reflecting the current address being fetched. This condition will remain through a subsequent phase two (\emptyset_2) in which the Ready signal is low. This feature allows microprocessor interfacing with low speed PROMS as well as fast (max. 2 cycle) Direct Memory Access (DMA). If Ready is low during a write cycle, it is ignored until the following read operation.

Interrupt Request (IRQ)

This TTL level input requests that an interrupt sequence begin within the microprocessor. The microprocessor will complete the current instruction being executed before recognizing the request. At that time, the interrupt mask bit in the Status Code Register will be examined. If the interrupt mask flag is not set, the microprocessor will begin an interrupt sequence. The Program Counter and Processor Status Register are stored in the stack. The microprocessor will be loaded from address FFFE, and program counter high from location FFFF, therefore transferring program control to the memory vector located at these addresses. The RDY signal must be in the high state for any interrupt' to be recognized. A 3KΩ external resistor should be used for proper wire-OR operation.

Non-Maskable Interrupt (NMI)

A negative going edge on this input requests that a non-maskable interrupt sequence be generated within the microprocessor. NMI is an unconditional interrupt. Following completion of the current instruction, the sequence of operations defined for IRQ will be performed, regardless of the interrupt mask flag status. The vector address loaded into the program counter, low and high, are locations FFFA and FFFB respectively, thereby transferring program control to the memory vector located at these addresses. The instructions loaded at these locations cause the microprocessor to branch to a non-maskable interrupt routine in memory.

NMI also requires an external 3KΩ resister to Vcc for proper wire-OR operations.

Inputs IRQ and NMI are hardware interrupt lines that are sampled during \emptyset_2 (phase 2) and will begin the appropriate interrupt routine on the \emptyset_1 (phase 1) following the completion of the current instruction.

Set Overflow Flag (S.O.)

A NEGATIVE going edge on this input sets the overflow bit in the Status Code Register. This signal is sampled on the trailing edge of \emptyset_1 .

SYNC

This output line is provided to identify those cycles in which the microprocessor is doing an OP CODE fetch. The SYNC line goes high during \emptyset , of an OP CODE fetch and stays high for the remainder of that cycle. If the RDY line is pulled low during the \emptyset , clock pulse in which SYNC went high, the processor will stop in its current state and will remain in the state until the RDY line goes high. In this manner, the SYNC signal can be used to control RDY to cause single instruction execution.

Reset

This input is used to reset or start the microprocessor from a power down condition. During the time that this line is held low, writing to or from the microprocessor is inhibited. When a positive edge is detected on the input, the microprocessor will immediately begin the reset sequence.

After a system initialization time of six clock cycles, the mask interrupt flag will be set and the microprocessor will load the program counter from the memory vector locations FFFC and FFFD. This is the start location for program control.

After Vcc reaches 4.75 volts in a power up routine, reset must be held low for at least two clock cycles. At this time the RW and (SYNC) signal will become valid.

When the reset signal goes high following these two clock cycles, the microprocessor will proceed with the normal reset procedure detailed above.





COMMON CHARACTERISTICS

ADDRESSING MODES

ACCUMULATOR ADDRESSING—This form of addressing is represented with a one byte instruction, implying an operation on the accumulator.

IMMEDIATE ADDRESSING—In immediate addressing, the operand is contained in the second byte of the instruction, with no further memory addressing required.

ABSOLUTE ADDRESSING—In absolute addressing, the second byte of the instruction specifies the eight low order bits of the effective address while the third byte specifies the eight high order bits. Thus, the absolute addressing mode allows access to the entire 65K bytes of addressable memory.

ZERO PAGE ADDRESSING — The zero page instructions allow for shorter code and execution times by only fetching the second byte of the instruction and assuming a zero high address byte. Careful use of the zero page can result in significant increase in code efficiency.

INDEXED ZERO PAGE ADDRESSING — (X, Y in dexing) — This form of addressing is used in conjunction with the index register and is referred to as "Zero Page, X" or "Zero Page, Y." The effective address is calculated by adding the second byte to the contents of the index register. Since this is a form of "Zero Page" addressing, the content of the second byte references a location in page zero. Additionally, due to the "Zero Page" addressing nature of this mode, no carry is added to the high order 8 bits of memory and crossing of page boundaries does not occur.

INDEXED ABSOLUTE ADDRESSING—(X, Y indexing)—This form of addressing is used in conjunction with X and Y index register and is referred to as "Absolute, X," and "Absolute, Y." The effective address is formed by adding the contents of X and Y to the address contained in the second and third bytes of the instruction. This mode allows the index register to contain the index or count value and the instruction to contain the base address. This type of indexing allows any location referencing and the index to modify multiple fields resulting in reduced coding and execution time. IMPLIED ADDRESSING—In the implied addressing mode, the address containing the operand is implicitly stated in the operation code of the instruction.

RELATIVE ADDRESSING—Relative addressing is used only with branch instructions and establishes a destination for the conditional branch.

The second byte of the instruction becomes the operand which is an "Offset" added to the contents of the lower eight bits of the program counter when the counter is set at the next instruction. The range of the offset is -128 to +127 bytes from the next instruction.

INDEXED INDIRECT ADDRESSING—In indexed indirect addressing (referred to as (Indirect, X)), the second byte of the instruction is added to the contents of the X index register, discarding the carry. The result of this addition points to a memory location on page zero whose contents is the low order eight bits of the effective address. The next memory location in page zero contains the high order eight bits of the effective address. Both memory locations specifying the high and low order bytes of the effective address must be in page zero.

INDIRECT INDEXED ADDRESSING —In indirect indexed addressing (referred to as (indirect), Y), the second byte of the instruction points to a memory location in page zero. The contents of this memory location is added to the contents of the Y index register, the result being the low order eight bits of the effective address. The carry from this addition is added to the contents of the next page zero memory location, the result being the high order eight bits of the effective address.

ABSOLUTE INDIRECT—The second byte of the instruction contains the low order eight bits of a memory location. The high order eight bits of that memory location is contained in the third byte of the instruction. The contents of the fully specified memory location is the low order byte of the effective address. The next memory location contains the high order byte of the effective address which is loaded into the sixteen bits of the program counter.

INSTRUCTION SET-ALPHABETIC SEQUENCE

ADC	Add Memory to Accumulator with Carry	LDA	Load Accumulator with Memory
AND	"AND" Memory with Accumulator	LDX	Load Index X with Memory
ASL	Shift left One Bit (Memory or Accumulator)	LDY	Load Index Y with Memory
BCC	Branch on Carry Clear	LSR	Shift One Bit Right (Memory or Accumulator)
BCS	Branch on Carry Set Branch on Besult Zero	NOP	No Operation
BIT	Test Bits in Memory with Accumulator	ORA	"OR" Memory with Accumulator
BNE	Branch on Result Ninus	PHA	Push Accumulator on Stack
BPL	Branch on Result Nus	PHP	Push Processor Status on Stack
BRK	Force Break	PLA	Puil Accumulator from Stack
BVC	Branch on Overflow Clear	PLP	Puil Processor Status from Stack
BVS	Branch on Overflow Set	ROL	Rotate One Bit Left (Memory or Accumulator)
CLC	Clear Carry Flag	ROR	Rotate One Bit Right (Memory or Accumulator)
CLD	Clear Decimal Mode	RTI	Return from Interrupt
CLI	Clear Interrupt Disable Bit	RTS	Return from Subroutine
CLV CMP CPX CPY DEC	Clear Overriow Flag Compare Memory and Accumulator Compare Memory and Index X Compare Memory and Index Y Decrement Memory by One	SBC SEC SED SEI SEI	Subtract Memory from Accumulator with Borrow Set Decimal Mode Set Interrupt Disable Status Store Accumulator in Memory
DEX	Decrement Index X by One	STX	Store Index X in Memory
DEY	Decrement Index Y by One		Store Index Y in Memory
EOR INC INX INY JMP JSR	"Exclusive-or" Memory with Accumulator Increment Memory by One Increment Index X by One Increment Index Y by One Jump to New Location Jump to New Location	TAX TAY TSX TXA TXS TYA	Transfer Accumulator to Index X Transfer Accumulator to Index Y Transfer Stack Pointer to Index X Transfer Index X to Accumulator Transfer Index X to Accumulator Transfer Index X to Stack Register Transfer Index Y to Accumulator



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	65C02 — 40 Pin Package
	Features of 65C02
N.C. 05 36 N.C. NMI-06 35 N.C.	65K Addressable Bytes of Memory (A0-A15) IRQ Interrupt
	On-the-chip Clock
A0 $\begin{array}{c} 9 \\ A1 \end{array} \begin{array}{c} 32 \\ 10 \end{array} \begin{array}{c} D1 \\ 31 \end{array} \begin{array}{c} D2 \\ D2 \end{array}$	TTL Level Single Phase Input
	Crystal Time Base Input
A4 S 13 28 C D5	SYNC Signal
A6 G 15 26 G D7	(can be used for single instruction execution) RDY Signal
A7 C 16 25 A15 A8 C 17 24 A14	(can be used to halt or single cycle execution)
	 Two Phase Output Clock for Timing of Support Chips
A11 20 21 VSS	NMI Interrupt
$\begin{array}{c c} RES & \blacksquare & 1 & 28 & \blacksquare & \emptyset_2 (OUT) \\ VSS & \blacksquare & 2 & 27 & \blacksquare & \emptyset_0 (IN) \\ IEC & \blacksquare & 3 & 26 & \blacksquare & RAW \end{array}$	65C03 — 28 Pin Package
	Features of 65C03
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	 4K Addressable Bytes of Memory (A0-A11) On-the-chin Clock
A3 C 9 20 D D5 A4 C 10 19 D D6	IRQ Interrupt
A5 C 11 18 D D7 A6 C 12 17 D A11	NMI Interrupt A Bit Bidirectional Data Bus
A7 = 13 16 = A10 A8 = 14 15 = A9	
$\begin{array}{c c} RES \blacksquare 1 & 28 \blacksquare \emptyset_2 (OUT) \\ VSS \blacksquare 2 & 27 \blacksquare \emptyset_0 (IN) \end{array}$	
IRO CO 3 26 P R/W VCC CC 4 25 P D0	65C04 — 28 Pin Package
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Features of 65C04
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	 • 8K Addressable Bytes of Memory (A0-A12)
A4 9 20 D5	On-the-chip Clock IPO Interrupt
	8 Bit Bidirectional Data Bus
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	
VSS C 2 27 b Ø ₀ (IN) RDY 3 26 b R/W IRO 4 25 b D0	65C05 — 28 Pin Package
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Features of 65C05
A1 = 7 22 = D3 A2 = 8 21 = D4	4K Addressable Bytes of Memory (A0-A11) Andressable Bytes of Memory (A0-A11)
	On-the-chip Clock IRQ Interrupt
	RDY Signal
	 8 Bit Bidirectional Data Bus
AB CT 14 15 CT A9	



MPS			
65	C	0	0
05		U	U

-		-	
1	28	þ	Ø2 (OUT)
2	27	Þ	Ø0 (IN)
3	.26	Þ	R/W
4	25	Þ	D0
5	24	╘	D1
6	23	ᄂ	D2
7	22	Þ	D3
8	21	F	D4
9	20	Þ	D5
10	19	Þ	D6
11	18	Þ	D7
12	17	늡	A11
13	16	5	A10
14	15	Ь	A9
	1 2 3 4 5 6 7 8 9 10 11 12 13 14	1 28 2 27 3 26 4 25 5 24 6 23 7 22 8 21 9 20 10 19 11 18 12 17 13 16 14 15	1 28 7 7 2 2 7 3 26 7 7 4 25 7 5 24 7 6 23 7 7 22 7 8 21 7 9 20 7 10 19 7 11 18 7 13 16 7 14 15 7

65C06 - 28 Pin Package

Features of 65C06

- 4K Addressable Bytes of Memory (A0-A11)
- On-the-chip Clock
- IRQ Interrupt
- Two phase output clock for timing of support chips
- 8 Bit Bidirectional Data Bus

RES 🗖	1	28	₽ Ø2 (OUT)	
vss 🗖	2	27	Þ Ø ₀ (IN)	
RDY 📼	3	26	P R/W	65C07 - 28 Pin Package
vcc 🗖	4	25	D D0	00CUT - 20 FIN FACKAge
A0 📼	5	24	D 1	
A1 🗖	6	23	D2	Features of 65C07
A2 🗖	7	22	D D3	
A3 🗖	8	21	D 4	 8K Addressable Bytes of Memory (A0-A12)
A4 🗖	9	20	⊐ D5	On-the-chip Clock
A5 🗖	10	19	D 6	PDV Signal
A6 🗖	11	18	D7	
A7 🗖	12	17	A12	8 Bit Bidirectional Data Bus
A8 🗖	13	16	A11	
A9 🗖	14	15	A10	

			 ~~	-	
VSS	q	1	40	Þ	RES
RDY	q	2	39	Þ	Ø2 (OUT)
Ø1(IN)	9	3	38	Þ	S.O.
ĪRQ	d	4	37	Þ	Ø2(IN)
VSS	d	5	36	Þ	DBE
NMI	P	6	35	Þ	N.C.
SYNC	d	7	34	Þ	R/W
VCC	q	8	33	Þ	D0
A0	q	9	32	ᄂ	D1
A1	q	10	31	Þ	D2
A2	q	1.	30	Þ	D3
A3	q	12	29	Þ	D4
A4	q	13	28	Þ	D5
A5	d	14	27	Þ	D6
A6	d	15	26	Þ	D7
A7	q	16	25	Þ	A15
A8	d	17	24	Þ	A14
A9	q	18	23	Þ	A13
A10	d	19	22	Þ	A12
A11	Ч	20	21	Ь	VSS
	L		 	J.	

65C12 - 40 Pin Package

Features of 65C12

- 65K Addressable Bytes of Memory (A0-A15)
- IRQ Interrupt
- NMI Interrupt
- RDY Signal
- 8 Bit Bidirectional Data Bus
- SYNC Signal
- Two phase clock input
- Data Bus Enable

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MPS 65C	K CMOS		
65C13 — 28 Pin Package Features of 65C13 • 4K Addressable Bytes of Memory (A0-A11) • Two phase clock input • TRQ Interrupt • NMI Interrupt • 8 Bit Bidirectional Data Bus	1 28 \overrightarrow{RES} 2 27 $\overrightarrow{\phi}_{2}(IN)$ 3 26 \overrightarrow{R} , W 4 25 $\overrightarrow{D0}$ 5 24 $\overrightarrow{D1}$ 6 23 $\overrightarrow{D2}$ 7 22 $\overrightarrow{D3}$ 8 21 $\overrightarrow{D4}$ 9 20 $\overrightarrow{D5}$ 10 19 $\overrightarrow{D6}$ 11 18 $\overrightarrow{D7}$ 12 17 $\overrightarrow{A11}$ 13 16 $\overrightarrow{A9}$	VSS U 1 0 1 1 1 1 1 2 1 1 2 1 1 1 2 3 1 1 1 2 3 1 1 1 1 2 3 1 1 1 1 1 2 3 1 1 1 1 1 1 1 1 1 1 1 1 1	
65C14 — 28 Pin Package Features of 65C14 • 8K Addressable Bytes of Memory (A0-A12) • Two phase clock input • TRQ Interrupt • 8 Bit Bidirectional Data Bus	1 28 $PRES$ 2 27 $M_{21}(N)$ 3 26 PRW 4 25 $PD0$ 5 24 $D11$ 6 23 $PD2$ 7 22 $PD3$ 8 21 $Dd4$ 9 20 $PD5$ 10 19 $D6$ 11 18 $D7$ 12 17 $A12$ 13 16 $A111$ 14 15 $A10$	VSS U 1 1 1 1 1 1 1 1	
65C15 — 28 Pin Package Features of 65C15 • 4K Addressable Bytes of Memory (A0-A11) • Two phase clock input • TRQ Interrupt • RDY Signal • 8 Bit Bidirectional Data Bus	1 28 \overrightarrow{RES} 2 27 \overrightarrow{RW} 3 26 \overrightarrow{RW} 4 25 $\overrightarrow{D0}$ 5 24 $\overrightarrow{D1}$ 6 23 $\overrightarrow{D2}$ 7 22 $\overrightarrow{D3}$ 8 21 $\overrightarrow{D4}$ 9 20 $\overrightarrow{D5}$ 10 19 $\overrightarrow{D6}$ 11 18 $\overrightarrow{D7}$ 12 17 $\overrightarrow{A11}$ 13 16 $\overrightarrow{A9}$	VSS RDY 1 2 0 1 1 2 0 1 1 2 0 1 1 2 0 1 1 2 0 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 0 1 1 1 2 5 5 A0 1 1 1 7 A 2 0 1 1 1 7 A 2 0 1 1 1 7 A 2 0 1 1 1 7 A 2 1 1 1 1 1 1 1 1 1 1 1 1 1	

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